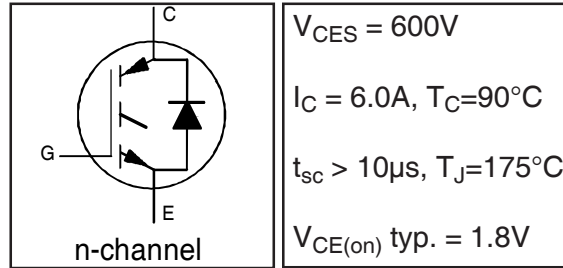


IRGIB6B60KDPbF

INSULATED GATE BIPOLAR TRANSISTOR WITH ULTRAFAST SOFT RECOVERY DIODE

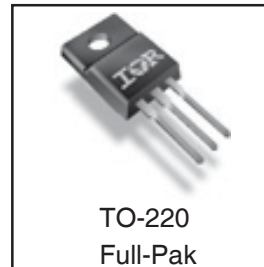
Features

- Low VCE (on) Non Punch Through IGBT Technology.
- Low Diode VF.
- 10µs Short Circuit Capability.
- Square RBSOA.
- Ultrasoft Diode Reverse Recovery Characteristics.
- Positive VCE (on) Temperature Coefficient.
- Lead-Free.



Benefits

- Benchmark Efficiency for Motor Control.
- Rugged Transient Performance.
- Low EMI.
- Excellent Current Sharing in Parallel Operation.



Absolute Maximum Ratings

| | Parameter | Max. | Units |
|---------------------------|--|-----------------------------------|-------|
| V_{CES} | Collector-to-Emitter Voltage | 600 | V |
| $I_C @ T_C = 25^\circ C$ | Continuous Collector Current | 11 | A |
| $I_C @ T_C = 100^\circ C$ | Continuous Collector Current | 7.0 | |
| I_{CM} | Pulse Collector Current (Ref.Fig.C.T.5) | 22 | |
| I_{LM} | Clamped Inductive Load current ① | 22 | |
| $I_F @ T_C = 25^\circ C$ | Diode Continuous Forward Current | 9.0 | |
| $I_F @ T_C = 100^\circ C$ | Diode Continuous Forward Current | 6.0 | |
| I_{FM} | Diode Maximum Forward Current | 18 | V |
| V_{ISOL} | RMS Isolation Voltage, Terminal to Case, t = 1 min | 2500 | |
| V_{GE} | Gate-to-Emitter Voltage | ±20 | W |
| $P_D @ T_C = 25^\circ C$ | Maximum Power Dissipation | 38 | |
| $P_D @ T_C = 100^\circ C$ | Maximum Power Dissipation | 19 | |
| T_J | Operating Junction and | -55 to +175 | °C |
| T_{STG} | Storage Temperature Range | | |
| | Soldering Temperature for 10 sec. | 300 (0.063 in. (1.6mm) from case) | |
| | Mounting Torque, 6-32 or M3 Screw | 10 lbf.in (1.1N.m) | |

Thermal / Mechanical Characteristics

| | Parameter | Min. | Typ. | Max. | Units |
|-----------------|---|------|------|------|-------|
| $R_{\theta JC}$ | Junction-to-Case- IGBT | — | — | 3.9 | °C/W |
| $R_{\theta JC}$ | Junction-to-Case- Diode | — | — | 6.0 | |
| $R_{\theta CS}$ | Case-to-Sink, flat, greased surface | — | 0.50 | — | |
| $R_{\theta JA}$ | Junction-to-Ambient, typical socket mount | — | — | 62 | |
| Wt | Weight | — | 2.0 | — | g |

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Electrical Characteristics @ T_J = 25°C (unless otherwise specified)

| | Parameter | Min. | Typ. | Max. | Units | Conditions | Ref.Fig. |
|--------------------------------------|---|------|------|------|-------|---|----------|
| V _{(BR)CES} | Collector-to-Emitter Breakdown Voltage | 600 | — | — | V | V _{GE} = 0V, I _C = 500μA | |
| ΔV _{(BR)CES/ΔT_J} | Temperature Coeff. of Breakdown Voltage | — | 0.30 | — | V/°C | V _{GE} = 0V, I _C = 1mA (25°C-150°C) | |
| V _{CE(on)} | Collector-to-Emitter Voltage | 1.50 | 1.80 | 2.20 | V | I _C = 5A, V _{GE} = 15V, T _J = 25°C | 5,6,7 |
| | | — | 2.20 | 2.50 | | I _C = 5A, V _{GE} = 15V, T _J = 150°C | 9,10,11 |
| | | — | 2.30 | 2.60 | | I _C = 5A, V _{GE} = 15V, T _J = 175°C | 9,10,11 |
| V _{GE(th)} | Gate Threshold Voltage | 3.5 | 4.5 | 5.5 | V | V _{CE} = V _{GE} , I _C = 250μA | 9,10,11 |
| ΔV _{GE(th)/ΔT_J} | Threshold Voltage temp. coefficient | — | -10 | — | mV/°C | V _{CE} = V _{GE} , I _C = 1mA (25°C-150°C) | 12 |
| g _f | Forward Transconductance | — | 3.0 | — | S | V _{CE} = 50V, I _C = 5.0A, PW = 80μs | |
| I _{CES} | Zero Gate Voltage Collector Current | — | 1.0 | 150 | μA | V _{GE} = 0V, V _{CE} = 600V | |
| | | — | 200 | 500 | | V _{GE} = 0V, V _{CE} = 600V, T _J = 150°C | |
| | | — | 720 | 1100 | | V _{GE} = 0V, V _{CE} = 600V, T _J = 175°C | |
| V _{FM} | Diode Forward Voltage Drop | — | 1.25 | 1.45 | V | I _F = 5.0A, V _{GE} = 0V | 8 |
| | | — | 1.20 | 1.40 | | I _F = 5.0A, V _{GE} = 0V, T _J = 150°C | |
| | | — | 1.15 | 1.35 | | I _F = 5.0A, V _{GE} = 0V, T _J = 175°C | |
| I _{GES} | Gate-to-Emitter Leakage Current | — | — | ±100 | nA | V _{GE} = ±20V, V _{CE} = 0V | |

Switching Characteristics @ T_J = 25°C (unless otherwise specified)

| | Parameter | Min. | Typ. | Max. | Units | Conditions | Ref.Fig. | |
|------------------------|--------------------------------------|-------------|------|------|-------|---|----------------------------|-------|
| Q _g | Total Gate Charge (turn-on) | — | 18.2 | 27.3 | nC | I _C = 5.0A | 23 | |
| Q _{ge} | Gate-to-Emitter Charge (turn-on) | — | 1.9 | 2.85 | | V _{CC} = 400V | CT1 | |
| Q _{gc} | Gate-to-Collector Charge (turn-on) | — | 9.2 | 13.8 | | V _{GE} = 15V | | |
| E _{on} | Turn-On Switching Loss | — | 110 | 210 | μJ | I _C = 5.0A, V _{CC} = 400V | CT4 | |
| E _{off} | Turn-Off Switching Loss | — | 135 | 245 | | V _{GE} = 15V, R _G = 100Ω, L = 1.4mH | | |
| E _{tot} | Total Switching Loss | — | 245 | 455 | | L _S = 150nH, T _J = 25°C ② | | |
| t _{d(on)} | Turn-On delay time | — | 25 | 34 | ns | I _C = 5.0A, V _{CC} = 400V | CT4 | |
| t _r | Rise time | — | 17 | 26 | | V _{GE} = 15V, R _G = 100Ω, L = 1.4mH | | |
| t _{d(off)} | Turn-Off delay time | — | 215 | 230 | | L _S = 150nH, T _J = 25°C | | |
| t _f | Fall time | — | 13.2 | 22 | | | | |
| E _{on} | Turn-On Switching Loss | — | 150 | 260 | | I _C = 5.0A, V _{CC} = 400V | | CT4 |
| E _{off} | Turn-Off Switching Loss | — | 190 | 300 | | V _{GE} = 15V, R _G = 100Ω, L = 1.4mH | | 13,15 |
| E _{tot} | Total Switching Loss | — | 340 | 560 | μJ | L _S = 150nH, T _J = 150°C ② | WF1,WF2 | |
| t _{d(on)} | Turn-On delay time | — | 28 | 37 | | I _C = 5.0A, V _{CC} = 400V | 14,16 | |
| t _r | Rise time | — | 17 | 26 | | V _{GE} = 15V, R _G = 100Ω, L = 1.4mH | CT4 | |
| t _{d(off)} | Turn-Off delay time | — | 240 | 255 | | L _S = 150nH, T _J = 150°C | WF1 | |
| t _f | Fall time | — | 18 | 27 | | | WF2 | |
| L _E | Internal Emitter Inductance | — | 7.5 | — | | nH | Measured 5 mm from package | |
| C _{ies} | Input Capacitance | — | 290 | 435 | pF | V _{GE} = 0V | 22 | |
| C _{oes} | Output Capacitance | — | 34 | 51 | | V _{CC} = 30V | | |
| C _{res} | Reverse Transfer Capacitance | — | 10 | 15 | | f = 1.0MHz | | |
| RB SOA | Reverse Bias Safe Operating Area | FULL SQUARE | | | | T _J = 150°C, I _C = 18A, V _p = 600V | 4 | |
| SC SOA | Short Circuit Safe Operating Area | 10 | — | — | μs | V _{CC} = 500V, V _{GE} = +15V to 0V, R _G = 100Ω | CT2 | |
| | | | | | | T _J = 150°C, V _p = 600V, R _G = 100Ω | CT3 | |
| I _{SC (PEAK)} | Peak Short Circuit Collector Current | — | 50 | — | A | V _{CC} = 360V, V _{GE} = +15V to 0V | WF4 | |
| E _{rec} | Reverse Recovery Energy of the Diode | — | 90 | 175 | μJ | T _J = 150°C | 17,18,19 | |
| t _{rr} | Diode Reverse Recovery Time | — | 70 | 91 | ns | V _{CC} = 400V, I _F = 5.0A, L = 1.4mH | 20,21 | |
| I _{rr} | Peak Reverse Recovery Current | — | 10 | 13 | A | V _{GE} = 15V, R _G = 100Ω, L _S = 150nH | CT4,WF3 | |
| Q _{rr} | Diode Reverse Recovery Charge | — | 350 | 455 | nC | di/dt = 400A/μs | | |

① V_{CC} = 80% (V_{CES}), V_{GE} = 20V, L = 100μH, R_G = 50Ω.

② Energy losses include "tail" and diode reverse recovery.

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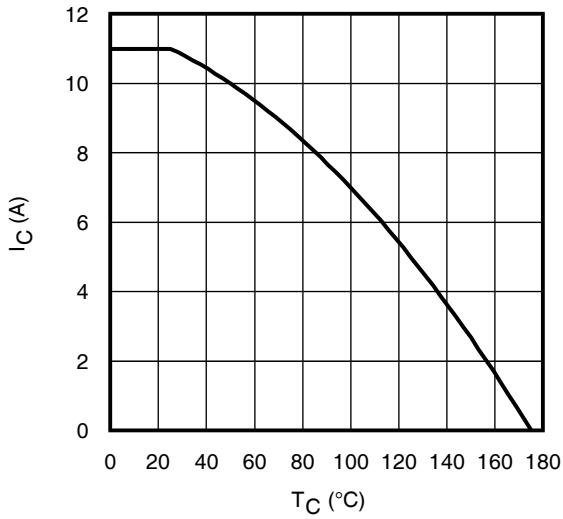


Fig. 1 - Maximum DC Collector Current vs. Case Temperature

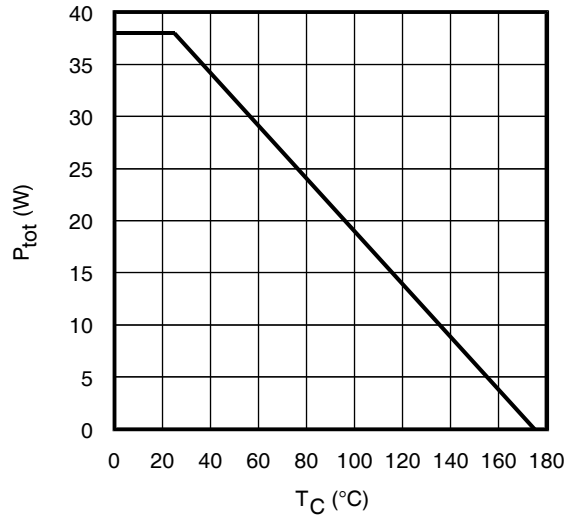


Fig. 2 - Power Dissipation vs. Case Temperature

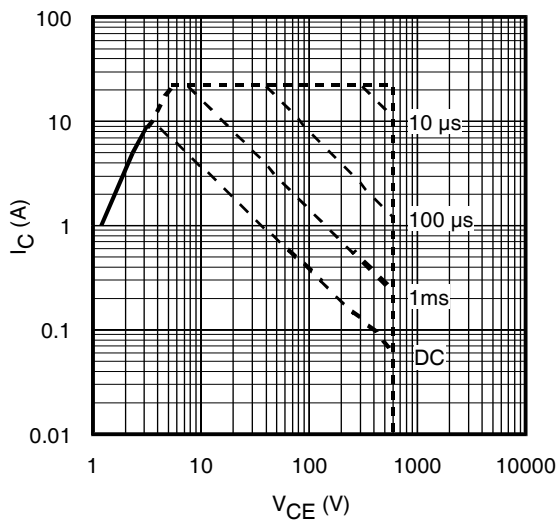


Fig. 3 - Forward SOA
 $T_C = 25^\circ\text{C}$; $T_J \leq 175^\circ\text{C}$

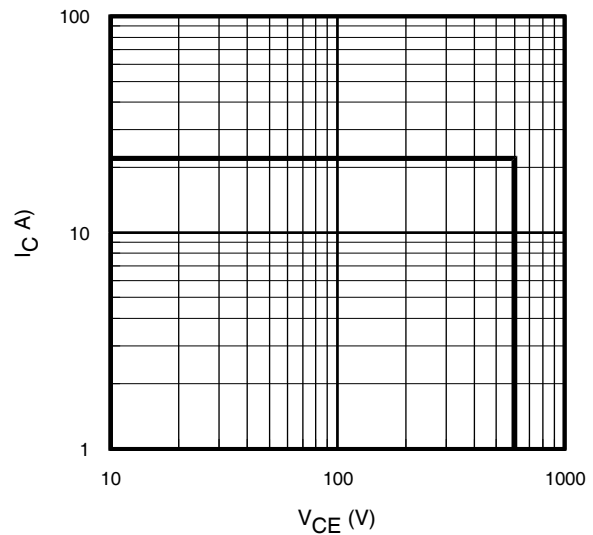


Fig. 4 - Reverse Bias SOA
 $T_J = 175^\circ\text{C}$; $V_{GE} = 15\text{V}$

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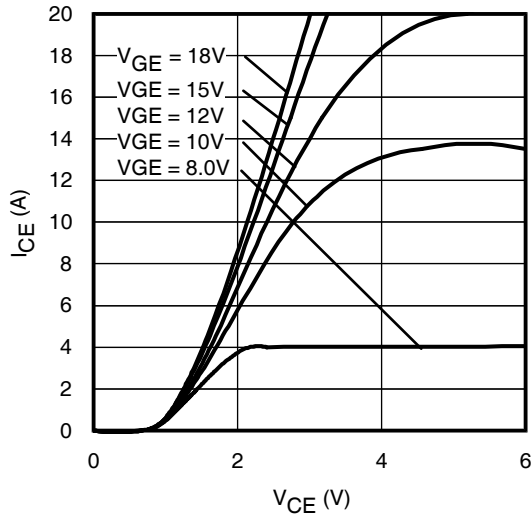


Fig. 5 - Typ. IGBT Output Characteristics
 $T_J = -40^\circ\text{C}$; $t_p = 80\mu\text{s}$

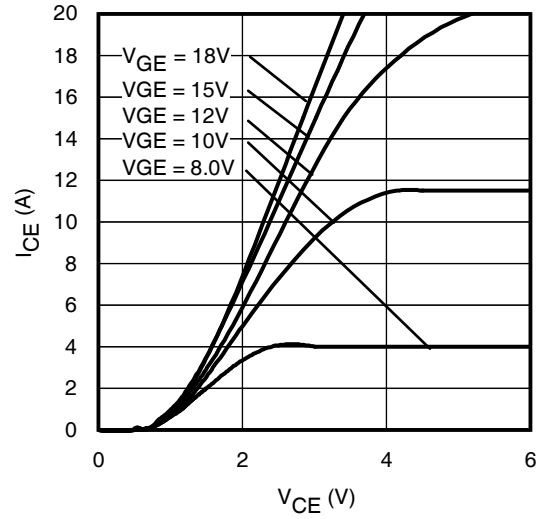


Fig. 6 - Typ. IGBT Output Characteristics
 $T_J = 25^\circ\text{C}$; $t_p = 80\mu\text{s}$

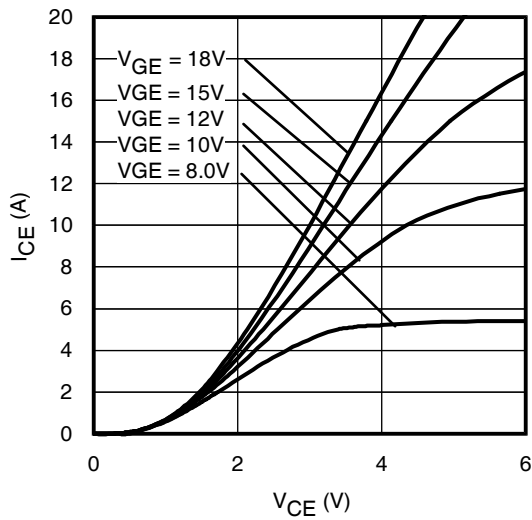


Fig. 7 - Typ. IGBT Output Characteristics
 $T_J = 150^\circ\text{C}$; $t_p = 80\mu\text{s}$

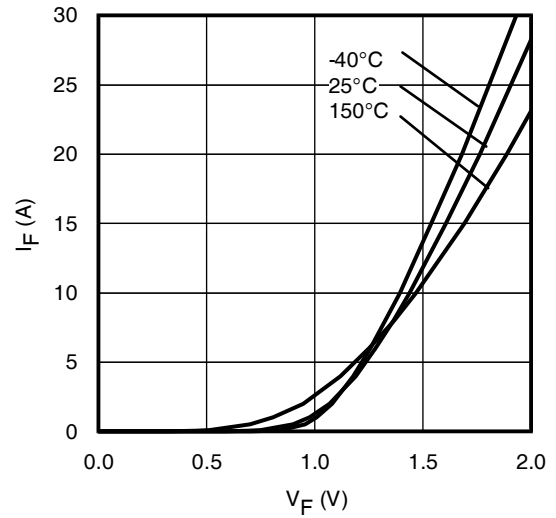


Fig. 8 - Typ. Diode Forward Characteristics
 $t_p = 80\mu\text{s}$

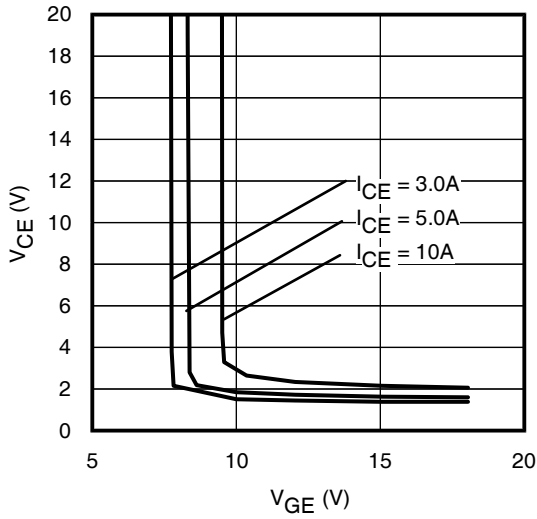


Fig. 9 - Typical V_{CE} vs. V_{GE}
 $T_J = -40^\circ\text{C}$

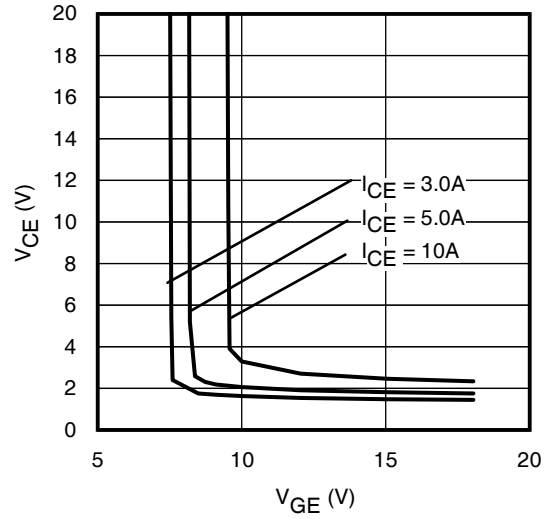


Fig. 10 - Typical V_{CE} vs. V_{GE}
 $T_J = 25^\circ\text{C}$

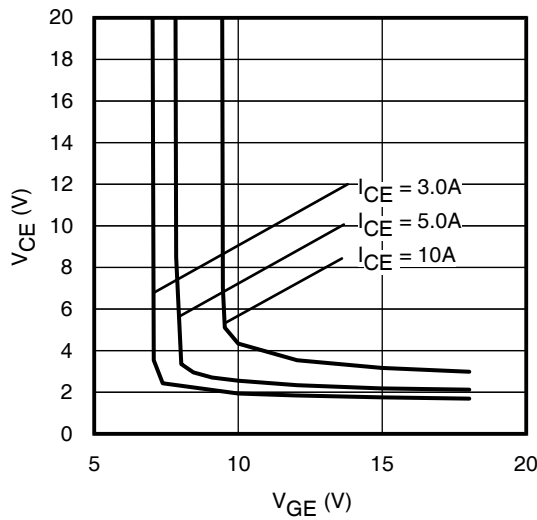


Fig. 11 - Typical V_{CE} vs. V_{GE}
 $T_J = 150^\circ\text{C}$

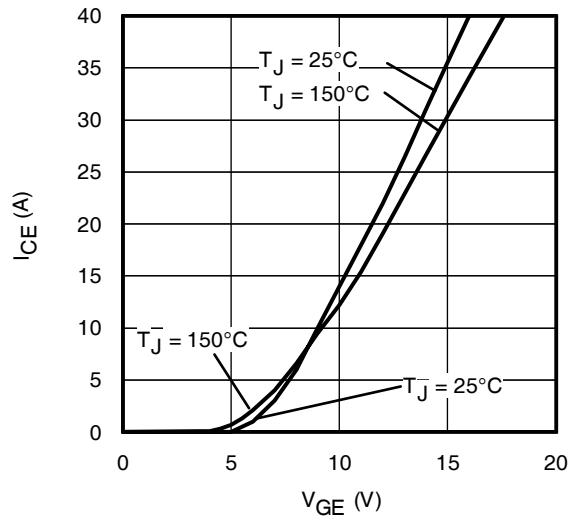


Fig. 12 - Typ. Transfer Characteristics
 $V_{CE} = 50\text{V}$; $t_p = 10\mu\text{s}$

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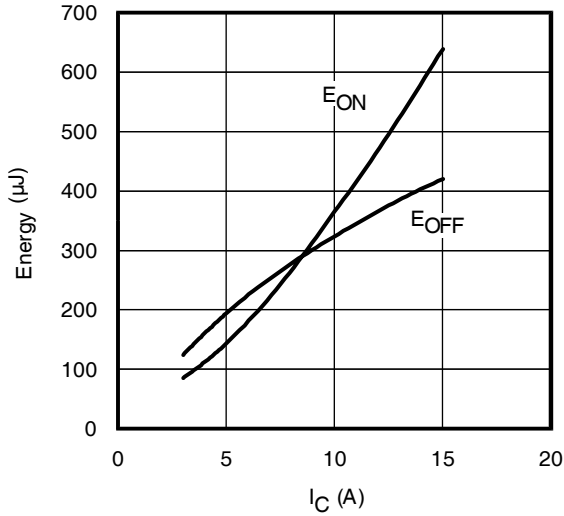


Fig. 13 - Typ. Energy Loss vs. I_C
 $T_J = 150^\circ\text{C}$; $L = 1.4\text{mH}$; $V_{CE} = 400\text{V}$
 $R_G = 100\Omega$; $V_{GE} = 15\text{V}$

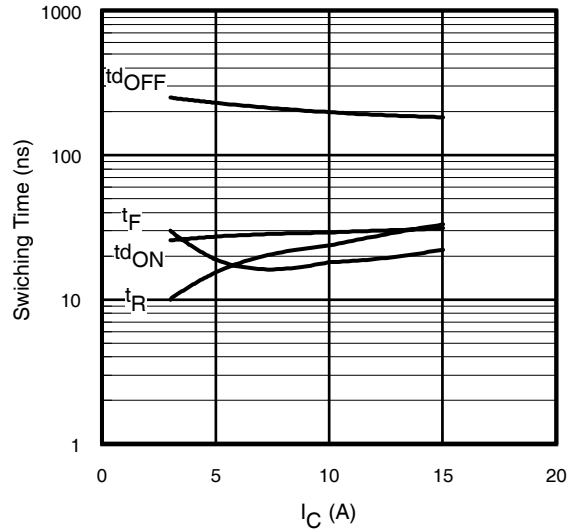


Fig. 14 - Typ. Switching Time vs. I_C
 $T_J = 150^\circ\text{C}$; $L = 1.4\text{mH}$; $V_{CE} = 400\text{V}$
 $R_G = 100\Omega$; $V_{GE} = 15\text{V}$

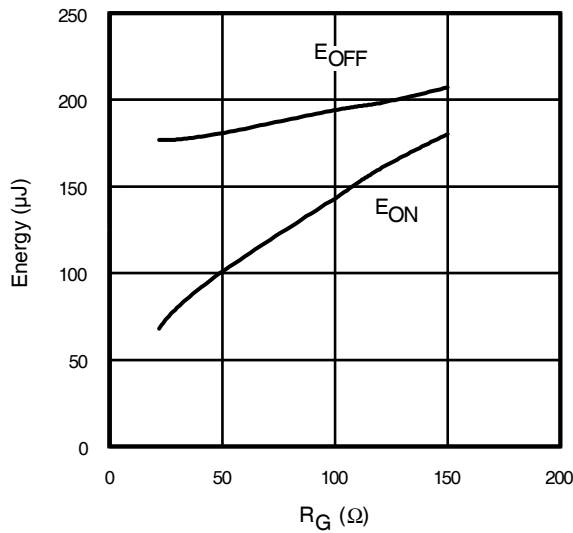


Fig. 15 - Typ. Energy Loss vs. R_G
 $T_J = 150^\circ\text{C}$; $L = 1.4\text{mH}$; $V_{CE} = 400\text{V}$
 $I_{CE} = 5.0\text{A}$; $V_{GE} = 15\text{V}$

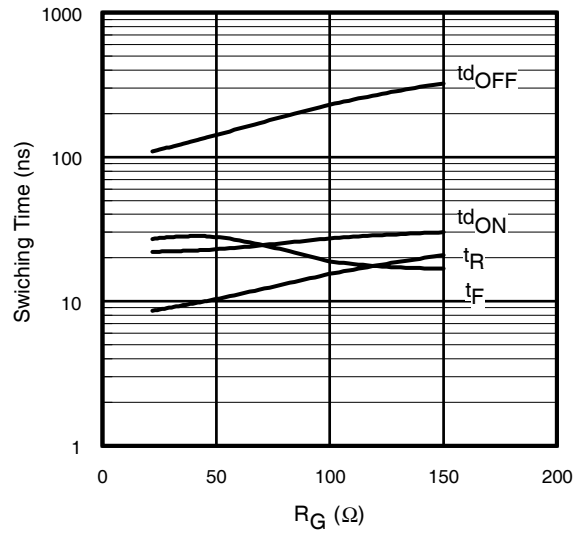


Fig. 16 - Typ. Switching Time vs. R_G
 $T_J = 150^\circ\text{C}$; $L = 1.4\text{mH}$; $V_{CE} = 400\text{V}$
 $I_{CE} = 5.0\text{A}$; $V_{GE} = 15\text{V}$

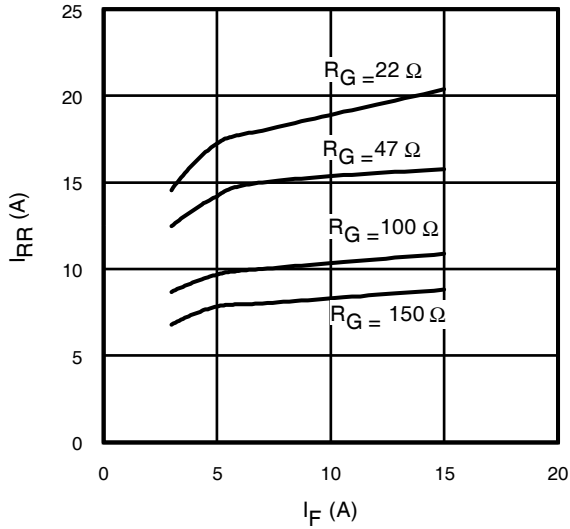


Fig. 17 - Typical Diode I_{RR} vs. I_F
 $T_J = 150^\circ\text{C}$

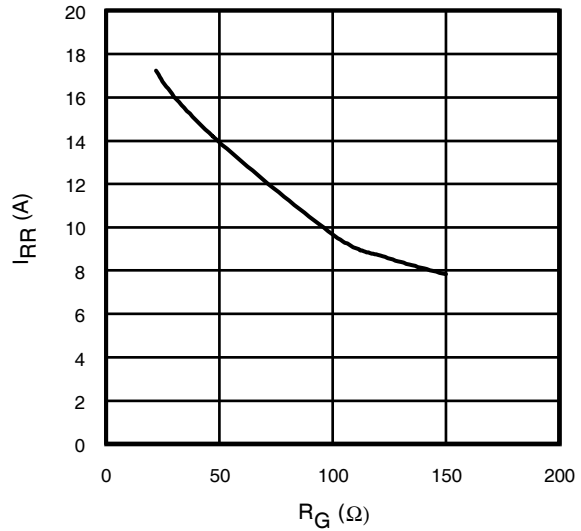


Fig. 18 - Typical Diode I_{RR} vs. R_G
 $T_J = 150^\circ\text{C}; I_F = 5.0\text{A}$

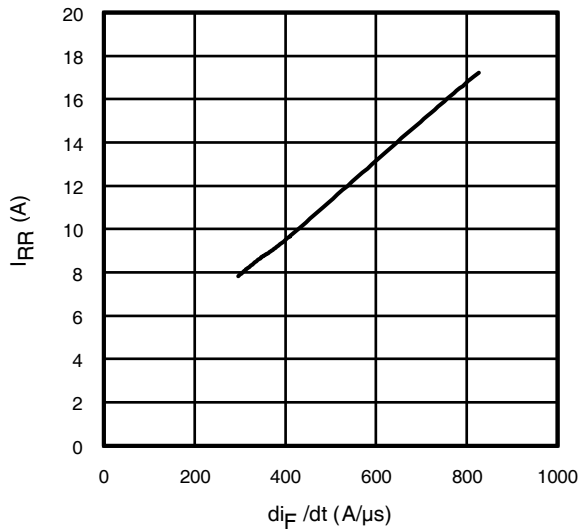


Fig. 19- Typical Diode I_{RR} vs. di_F/dt
 $V_{CC} = 400\text{V}; V_{GE} = 15\text{V};$
 $I_{CE} = 5.0\text{A}; T_J = 150^\circ\text{C}$

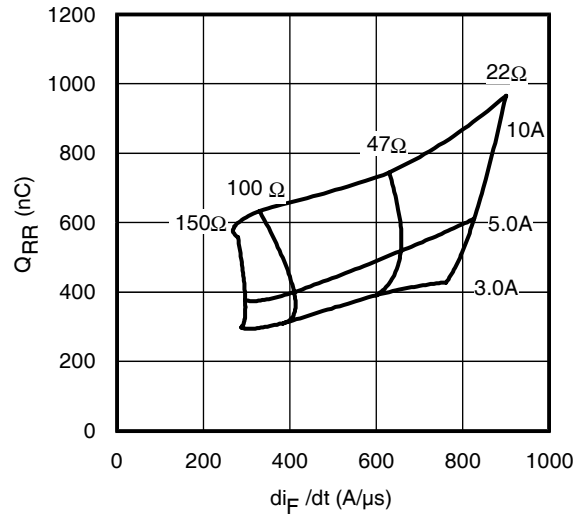


Fig. 20 - Typical Diode Q_{RR}
 $V_{CC} = 400\text{V}; V_{GE} = 15\text{V}; T_J = 150^\circ\text{C}$

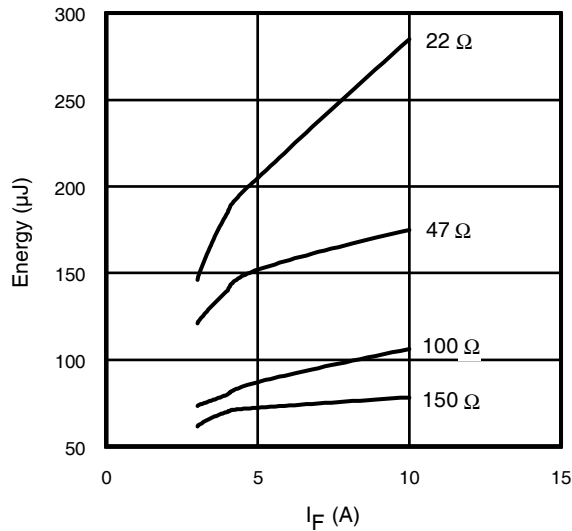


Fig. 21 - Typical Diode E_{RR} vs. I_F
 $T_J = 150^\circ\text{C}$

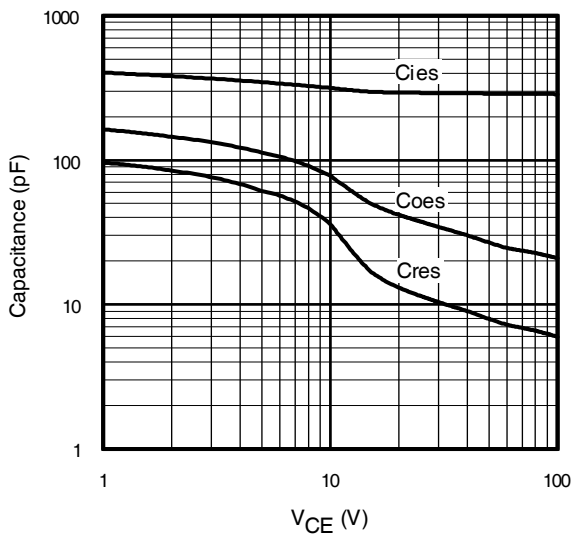


Fig. 22- Typ. Capacitance vs. V_{CE}
 $V_{GE} = 0\text{V}$; $f = 1\text{MHz}$

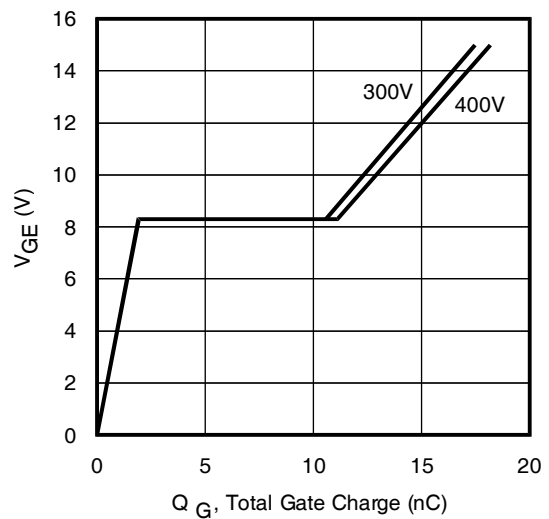


Fig. 23 - Typical Gate Charge vs. V_{GE}
 $I_{CE} = 5.0\text{A}$; $L = 600\mu\text{H}$

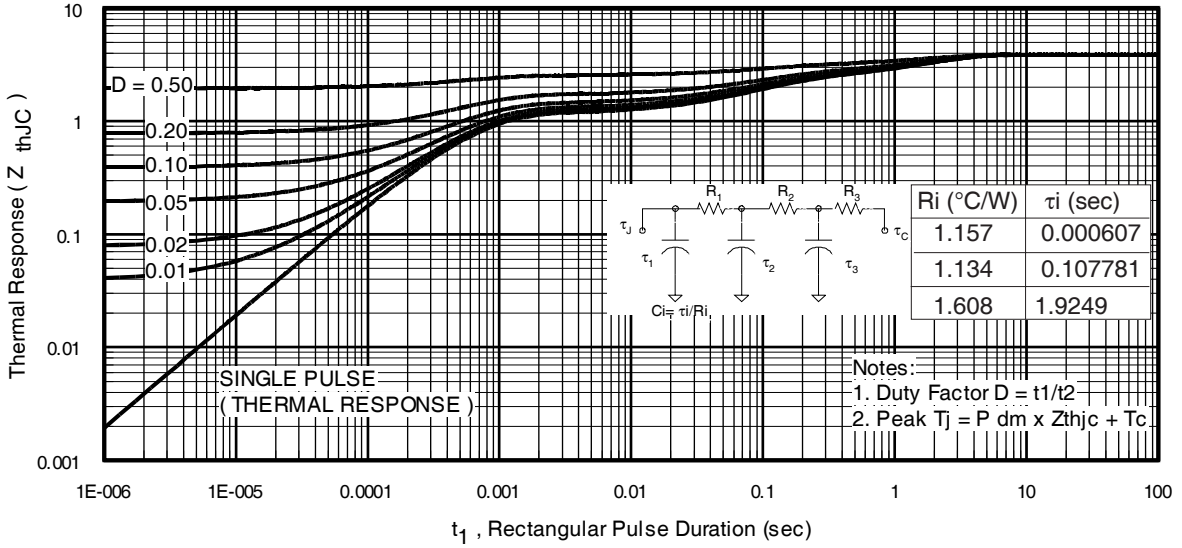


Fig 24. Maximum Transient Thermal Impedance, Junction-to-Case (IGBT)

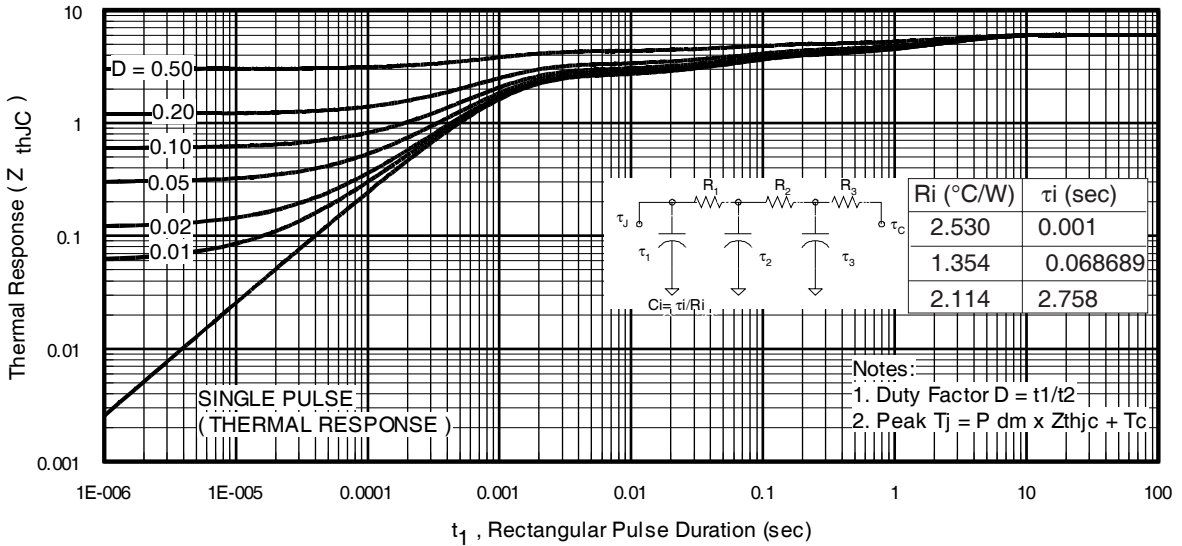


Fig 25. Maximum Transient Thermal Impedance, Junction-to-Case (DIODE)

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International
IR Rectifier

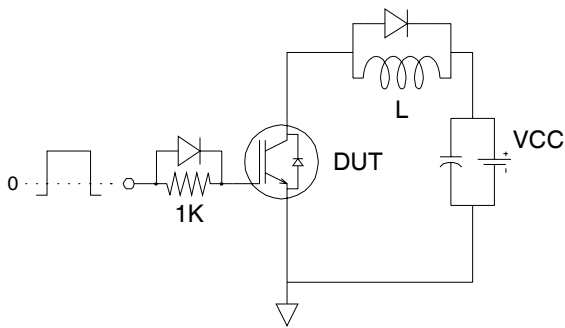


Fig.C.T.1 - Gate Charge Circuit (turn-off)

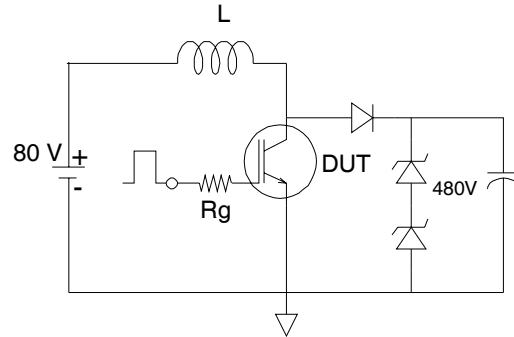


Fig.C.T.2 - RBSOA Circuit

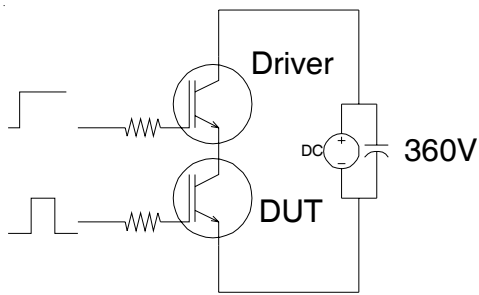


Fig.C.T.3 - S.C.SOA Circuit

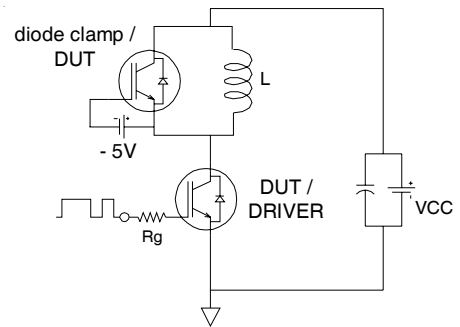


Fig.C.T.4 - Switching Loss Circuit

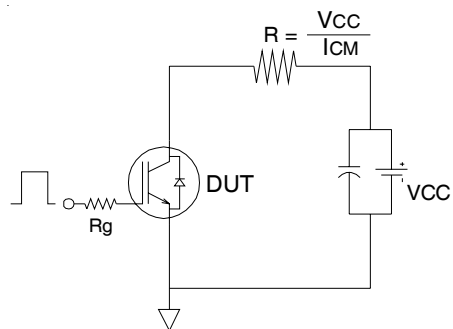


Fig.C.T.5 - Resistive Load Circuit

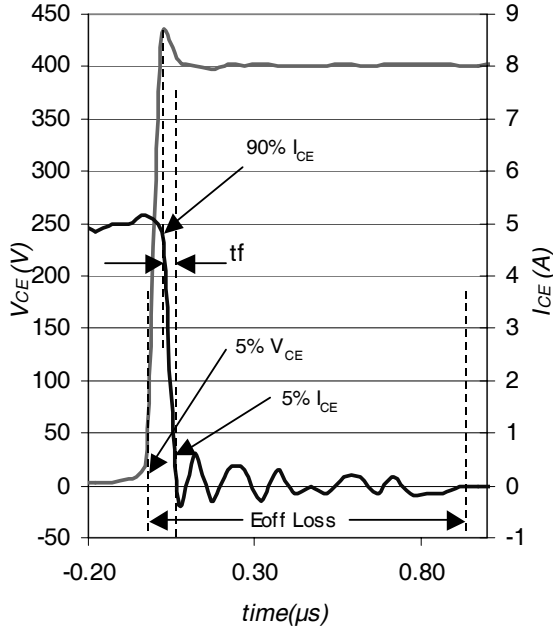


Fig. WF1- Typ. Turn-off Loss Waveform
@ $T_J = 150^\circ\text{C}$ using Fig. CT.4

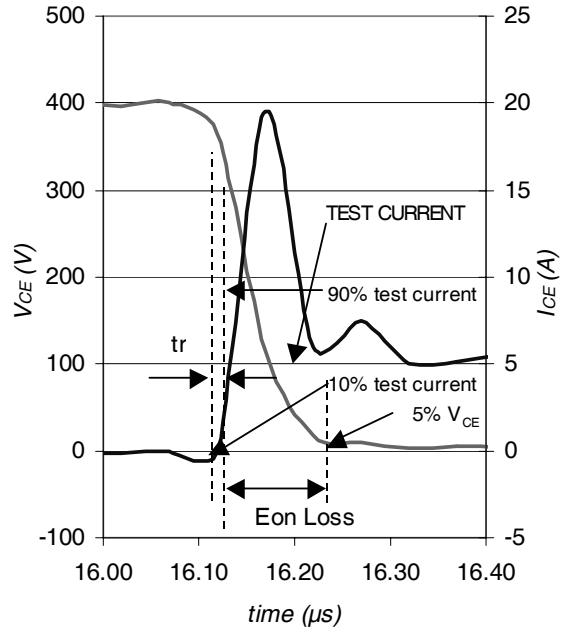


Fig. WF2- Typ. Turn-on Loss Waveform
@ $T_J = 150^\circ\text{C}$ using Fig. CT.4

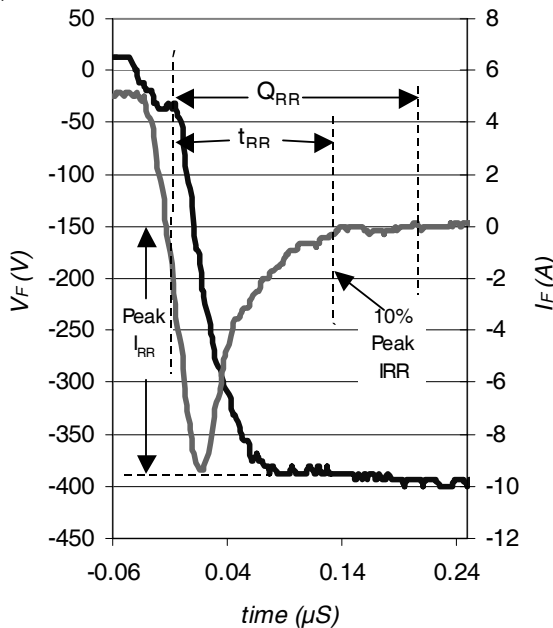


Fig. WF3- Typ. Diode Recovery Waveform
@ $T_J = 150^\circ\text{C}$ using Fig. CT.4

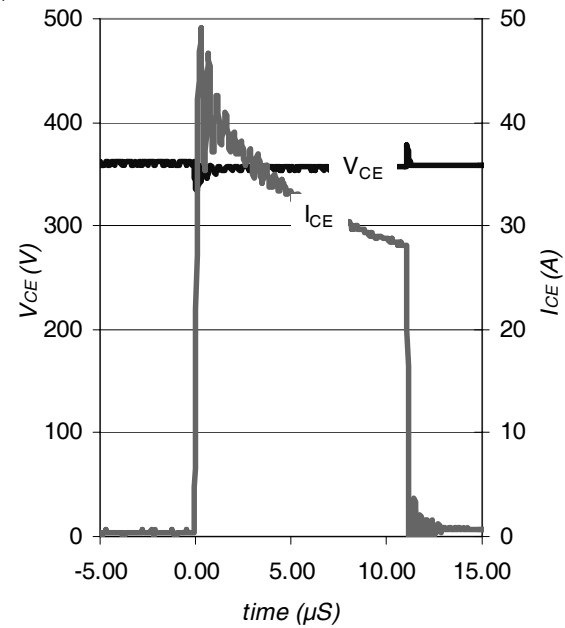


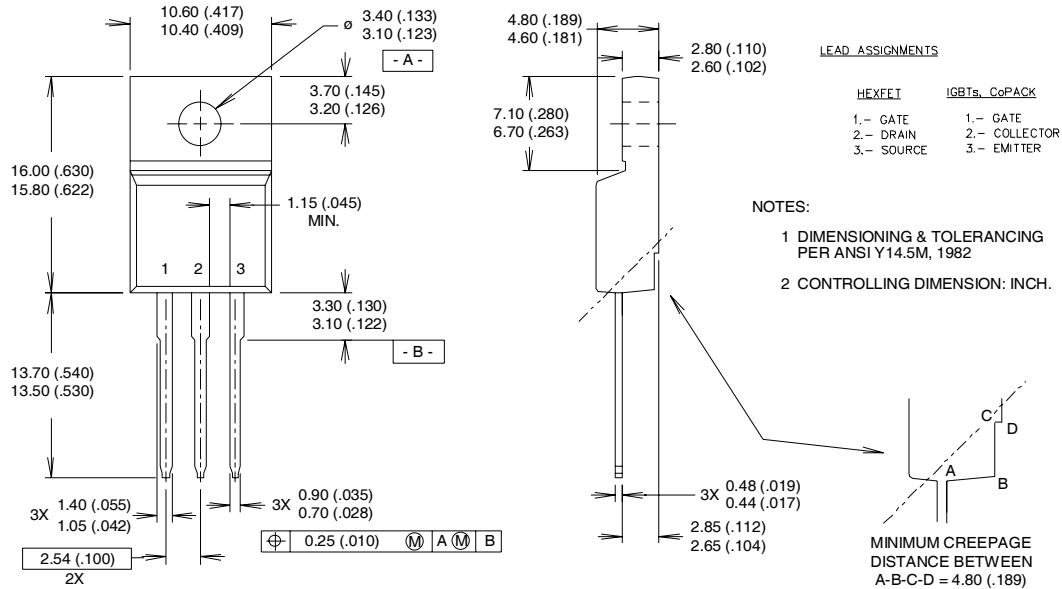
Fig. WF4- Typ. S.C Waveform
@ $T_J = 150^\circ\text{C}$ using Fig. CT.3

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TO-220 Full-Pak Package Outline

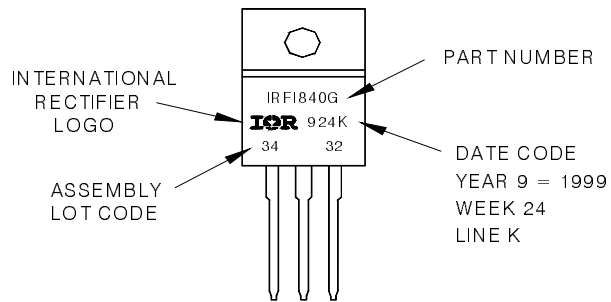
Dimensions are shown in millimeters (inches)



TO-220 Full-Pak Part Marking Information

EXAMPLE: THIS IS AN IRFI840G
 WITH ASSEMBLY
 LOT CODE 3432
 ASSEMBLED ON WW 24 1999
 IN THE ASSEMBLY LINE "K"

Note: "P" in assembly line position indicates "Lead-Free"



TO-220 Full-Pak package is not recommended for Surface Mount Application

Data and specifications subject to change without notice.
 This product has been designed and qualified for the Industrial market.
 Qualification Standards can be found on IR's Web site.



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 TAC Fax: (310) 252-7903

Visit us at www.irf.com for sales contact information.05/04